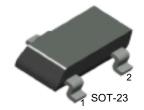


KSC2859

Low Frequency Power Amplifier

Complement to KSA1182



1. Base 2. Emitter 3. Collector

Rev. A, February 2000

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

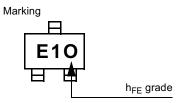
Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	35	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	500	mA
P _C	Collector Dissipation	150	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_a =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I _{CEO}	Collector Cut-off Current	V_{CB} =35V, I_{E} =0			0.1	μΑ
I _{EBO}	Emitter Cut-off Current	V _{EB} =5V, I _C =0			0.1	μΑ
h _{FE1} h _{FE2}	DC Current Gain	V _{CE} =1V, I _C =100mA V _{CE} =6V, I _C =400mA	70 25		240	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =100mA, I _B =10mA		0.1	0.25	V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =1V, I _C =100mA		0.8	1.0	V
f _T	Current Gain-Bandwidth Product	V _{CE} =6V, I _C =20mA		300		MHz
C _{ob}	Output Capacitance	V _{CB} =6V, I _E =0, f=1MHz		7		pF

h_{FE1} Classification

Classification	0	Y	
h _{FE1}	70 ~ 140	120 ~ 240	



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Typical Characteristics

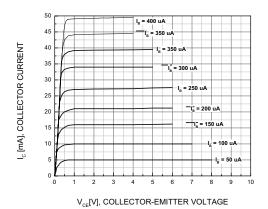


Figure 1. Static Characteristics

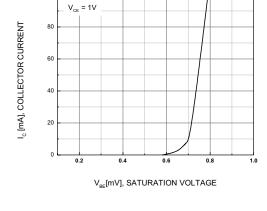


Figure 2. Base-Emitter On Voltage

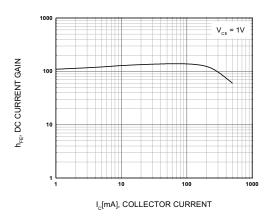


Figure 3. DC Current Gain

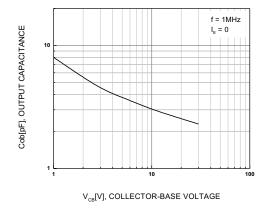


Figure 4. Output Capacitance

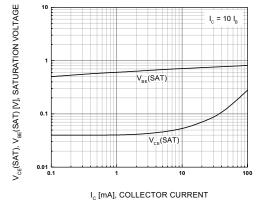
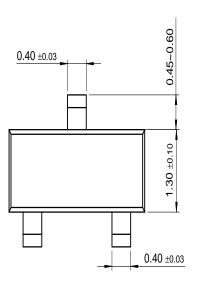


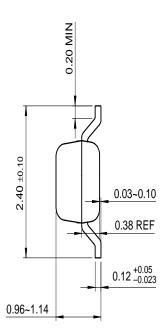
Figure 5. Saturation Voltage

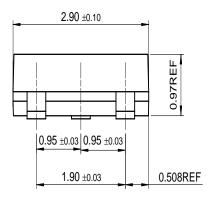
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Package Demensions

SOT-23







Dimensions in Millimeters

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